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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Nobuaki MITAMURA et al.			
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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	

FOREIGN PATENT DOCUMENTS						
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS		
<i>F.H.</i> 1	JP A 11-147786 w/ abst & transl	6/2/1999	JAPAN			
<i>F.H.</i> 2	JP A 2000-178099 w/ abst & transl	6/27/2000	JAPAN			
<i>F.H.</i> 3	JP A 2002-201093 w/ abst & transl	7/16/2002	JAPAN			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>F.H.</i>	4	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643 {1982}
<i>F.H.</i>	5	DUPRET et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No. 9, pp. 1849-1871 {1990}

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>6/27/2006</i>
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